

MC74HC175A

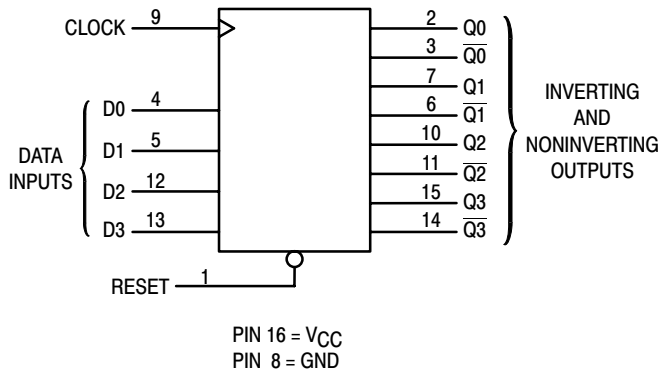
Quad D Flip-Flop with Common Clock and Reset High-Performance Silicon-Gate CMOS

The MC74HC175A is identical in pinout to the LS175. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of four D flip-flops with common Reset and Clock inputs, and separate D inputs. Reset (active-low) is asynchronous and occurs when a low level is applied to the Reset input. Information at a D input is transferred to the corresponding Q output on the next positive going edge of the Clock input.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity 166 FETs or 41.5 Equivalent Gates

LOGIC DIAGRAM



FUNCTION TABLE

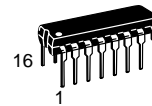
Inputs			Outputs	
Reset	Clock	D	Q	\bar{Q}
L	X	X	L	H
H	\nearrow	H	H	L
H	\searrow	L	L	H
H	L	X	No Change	



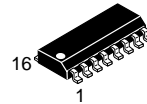
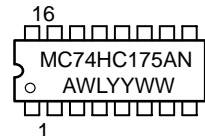
ON Semiconductor

<http://onsemi.com>

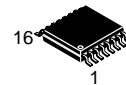
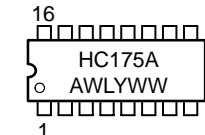
MARKING DIAGRAMS



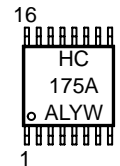
PDIP-16
N SUFFIX
CASE 648



SO-16
D SUFFIX
CASE 751B

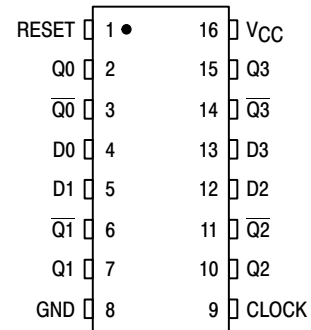


TSSOP-16
DT SUFFIX
CASE 948F



A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping
MC74HC175AN	PDIP-16	2000 / Box
MC74HC175AD	SOIC-16	48 / Rail
MC74HC175ADR2	SOIC-16	2500 / Reel
MC74HC175ADT	TSSOP-16	96 / Rail
MC74HC175ADTR2	TSSOP-16	2500 / Reel

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: - 10 mW/ C from 65 to 125 C

SOIC Package: - 7 mW/ C from 65 to 125 C

TSSOP Package: - 6.1 mW/ C from 65 to 125 C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V 0 V _{CC} = 3.0 V 0 V _{CC} = 4.5 V 0 V _{CC} = 6.0 V	1000 600 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25 C	≤ 85 C	≤ 125 C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	1.5	1.5	1.5	V
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0	0.5	0.5	0.5	V
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.80	1.80	1.80	
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	3.0	2.48	2.34	2.20	
			4.5	3.98	3.84	3.70	
			6.0	5.48	5.34	5.20	

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25 C	≤ 85 C	≤ 125 C	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 2.4 mA I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	3.0	0.26	0.33	0.40	
			4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			- 55 to 25 C	≤ 85 C	≤ 125 C	
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0	6	4.8	4	MHz
		3.0	10	8.0	6	
		4.5	30	24	20	
		6.0	35	28	24	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q or \bar{Q} (Figures 1 and 4)	2.0	150	190	225	ns
		3.0	75	90	110	
		4.5	26	32	38	
		6.0	22	28	33	
t _{PHL}	Maximum Propagation Delay, Reset to Q or \bar{Q} (Figures 2 and 4)	2.0	125	155	190	ns
		3.0	70	85	110	
		4.5	22	27	34	
		6.0	19	24	30	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0	75	95	110	ns
		3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTES:

- For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C _{PD}	Power Dissipation Capacitance (Per Flip-Flop)*	Typical @ 25°C, V _{CC} = 5.0 V	
		35	
		pF	

* Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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TIMING REQUIREMENTS (Input $t_r = t_f = 6$ ns)

Symbol	Parameter	VCC V	Guaranteed Limit			Unit
			- 55 to 25 C	≤ 85 C	≤ 125 C	
t_{su}	Minimum Setup Time, Data to Clock (Figure 3)	2.0	100	125	150	ns
		3.0	45	65	85	
		4.5	20	25	30	
		6.0	17	21	26	
t_h	Minimum Hold Time, Clock to Data (Figure 3)	2.0	5	5	5	ns
		3.0	3	3	3	
		4.5	3	3	3	
		6.0	3	3	3	
t_{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0	100	125	150	ns
		3.0	45	65	85	
		4.5	20	25	30	
		6.0	17	21	26	
t_w	Minimum Pulse Width, Clock (Figure 1)	2.0	80	100	120	ns
		3.0	45	65	85	
		4.5	16	20	24	
		6.0	14	17	20	
t_w	Minimum Pulse Width, Reset (Figure 2)	2.0	80	100	120	ns
		3.0	45	65	85	
		4.5	16	20	24	
		6.0	14	17	20	
t_r, t_f	Maximum Input Rise and Fall Times (Figure 1)	2.0	1000	1000	1000	ns
		3.0	800	800	800	
		4.5	500	500	500	
		6.0	400	400	400	

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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SWITCHING WAVEFORMS

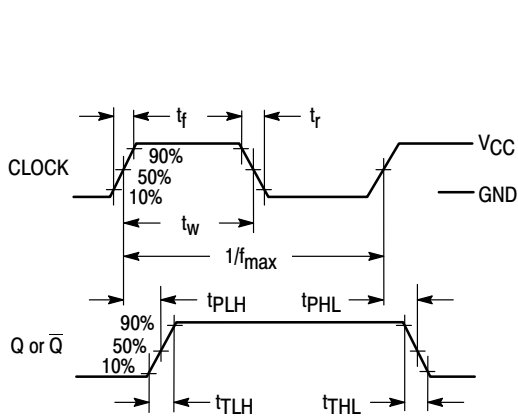


Figure 1.

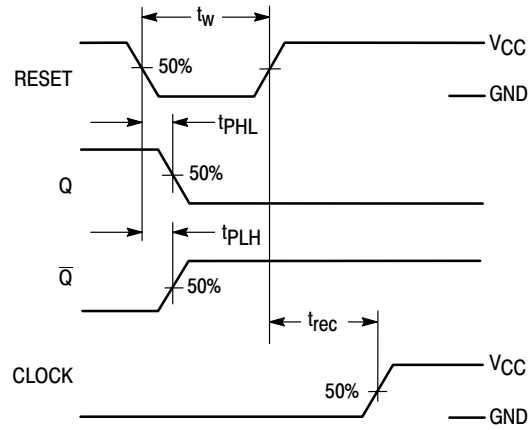


Figure 2.

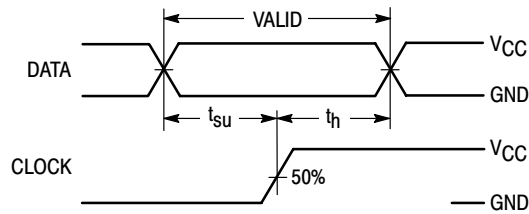
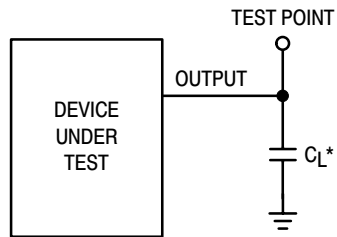


Figure 3.

TEST CIRCUIT



*Includes all probe and jig capacitance

Figure 4.

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EXPANDED LOGIC DIAGRAM

